

# GNTA - GNTM

# GLASS PASSIVATED JUNCTION SILICON SURFACE MOUNT

PRV : 50 - 1000 Volts

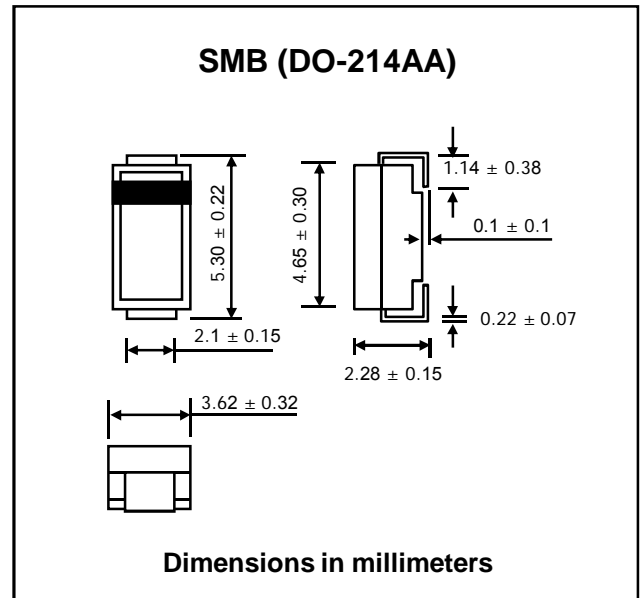
Io : 2.5 Amperes

### FEATURES :

- \* Glass passivated chip
- \* High current capability
- \* High reliability
- \* Low leakage
- \* Low forward voltage drop
- \* Pb / RoHS Free

### MECHANICAL DATA :

- \* Case : SMB Molded plastic
- \* Epoxy : UL94V-0 rate flame retardant
- \* Lead : Lead Formed for Surface Mount
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.1079 gram



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

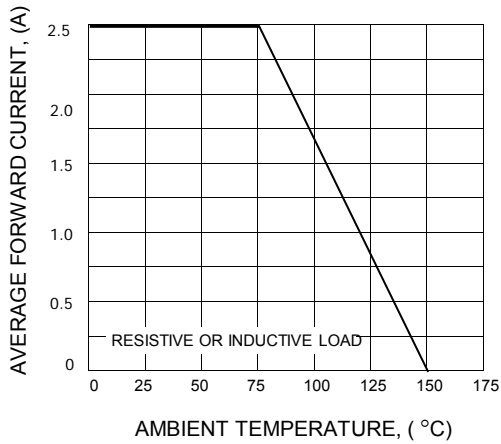
RATING	SYMBOL	GNTA	GNTB	GNTD	GNTG	GNTJ	GNTK	GNTM	UNIT
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward Current $T_a = 75\text{ }^\circ\text{C}$	$I_{F(AV)}$	2.5							A
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	$I_{FSM}$	150							A
Maximum Instantaneous Forward Voltage at $I_F = 2.5\text{ A}$ .	$V_F$	1.1							V
Maximum DC Reverse Current at rated DC Blocking Voltage	$I_R$	5.0							$\mu\text{A}$
	$I_{R(H)}$	50							$\mu\text{A}$
Typical Junction Capacitance (Note1)	$C_J$	35							pF
Operating Junction Temperature Range	$T_J$	- 65 to + 150							$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	- 65 to + 150							$^\circ\text{C}$

**Note :**

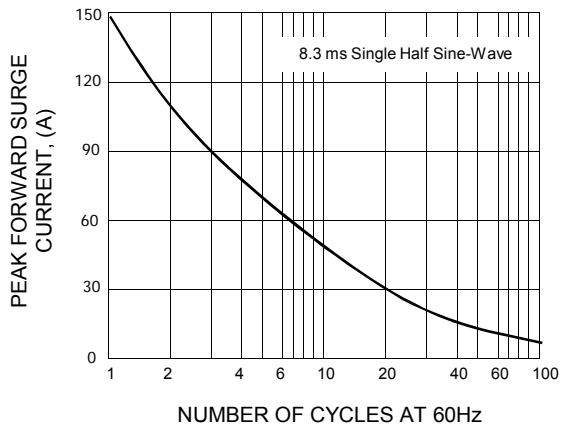
(1) Measured at 1.0 MHz and applied reverse voltage of 4.0 V.

**RATING AND CHARACTERISTIC CURVES ( GNTA - GNTM )**

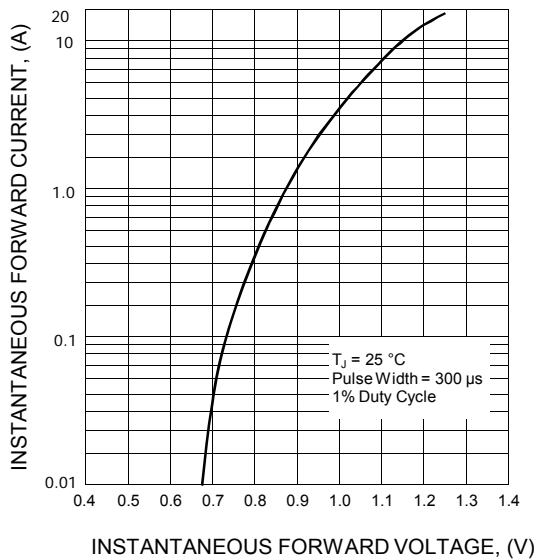
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**

